

SANYO	No.4744	2SJ255
		P-Channel MOS Silicon FET Very High-Speed Switching Applications

Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Micaless package facilitating easy mounting.

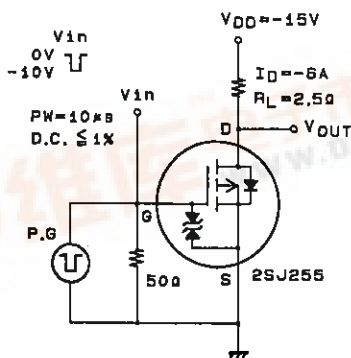
Absolute Maximum Ratings at Ta = 25°C

			unit
Drain-to-Source Voltage	V _{DSS}	-30	V
Gate-to-Source Voltage	V _{GS}	±20	V
Drain Current(DC)	I _D	-10	A
Drain Current(Pulse)	I _{DP}	PW ≤ 10μs, duty cycle ≤ 1%	-40 A
Allowable Power Dissipation	P _D	Tc = 25°C	2.0 W
			25 W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics at Ta = 25°C

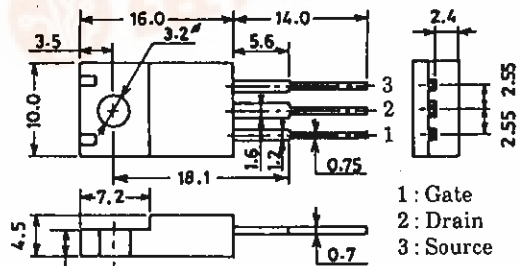
			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D = -1mA, V _{GS} = 0	-30			V
G-S Breakdown Voltage	V _{(BR)GSS}	I _G = ±100μA, V _{DS} = 0	±20			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} = -30V, V _{GS} = 0			-100	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = ±16V, V _{DS} = 0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} = -10V, I _D = -1mA	-1.0		-2.0	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = -10V, I _D = -6A	5	8		S
Static Drain-to-Source ON-State Resistance	R _{DS(on)}	I _D = -6A, V _{GS} = -10V		0.07	0.095	Ω
ON-State Resistance	R _{DS(on)}	I _D = -6A, V _{GS} = -4V		0.095	0.13	Ω
Input Capacitance	C _{iss}	V _{DS} = -10V, f = 1MHz		1300		pF
Output Capacitance	C _{oss}	V _{DS} = -10V, f = 1MHz		780		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = -10V, f = 1MHz		290		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		16		ns
Rise Time	t _r	∕		60		ns
Turn-OFF Delay Time	t _{d(off)}	∕		300		ns
Fall Time	t _f	∕		250		ns
Diode Forward Voltage	V _{SD}	I _S = -10A, V _{GS} = 0	-1.0	-1.5		V

Switching Time Test Circuit



Package Dimensions 2063A

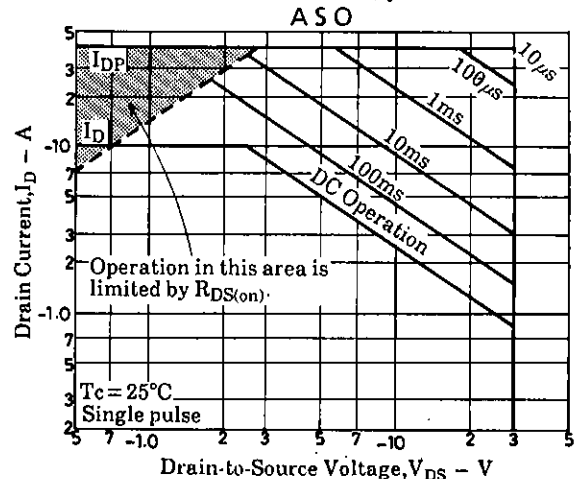
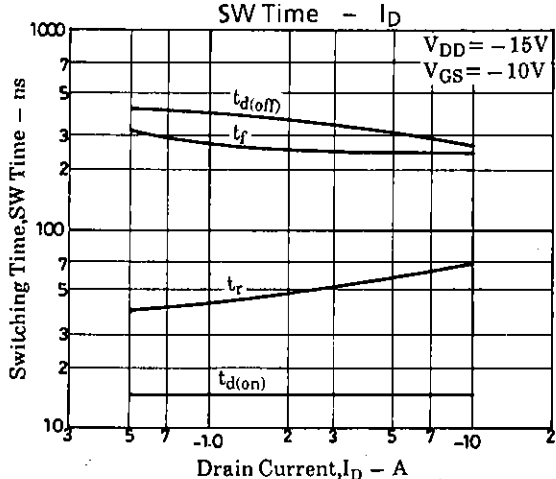
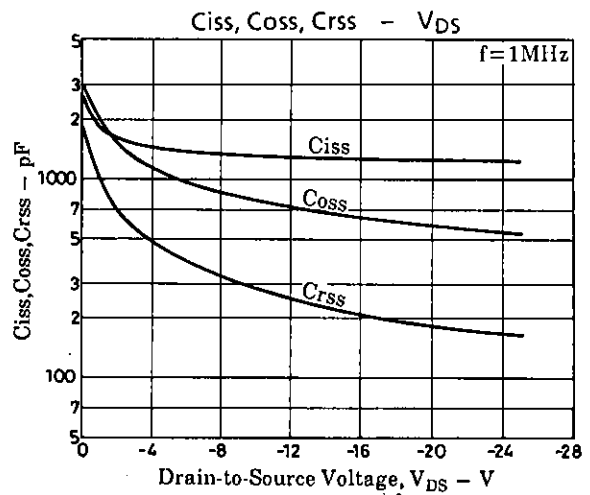
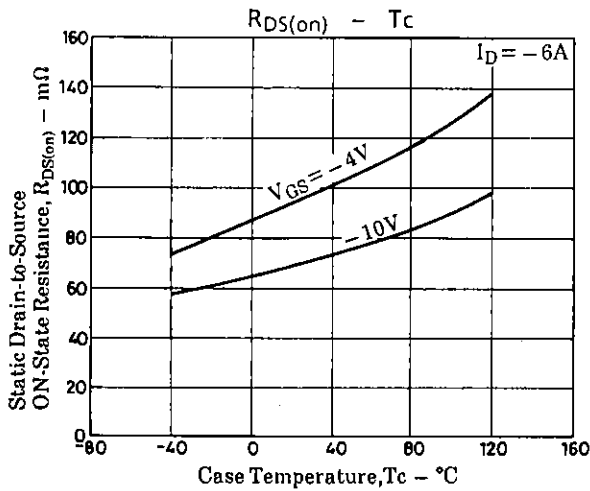
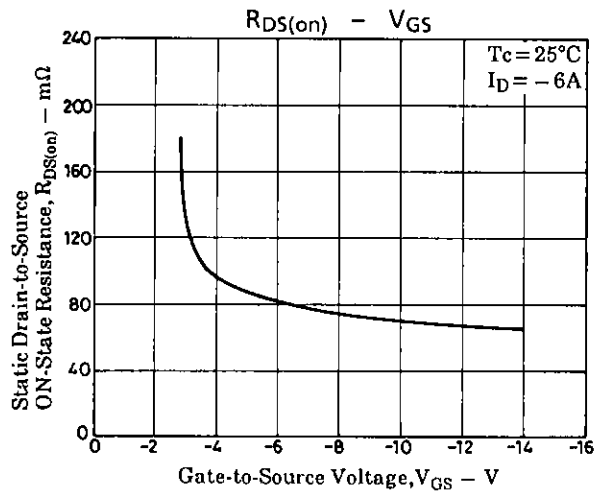
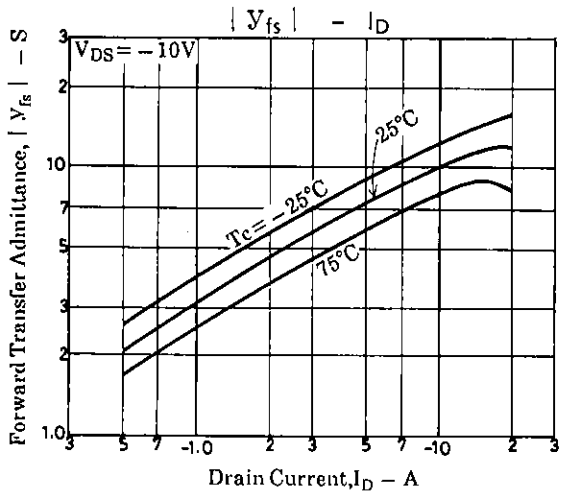
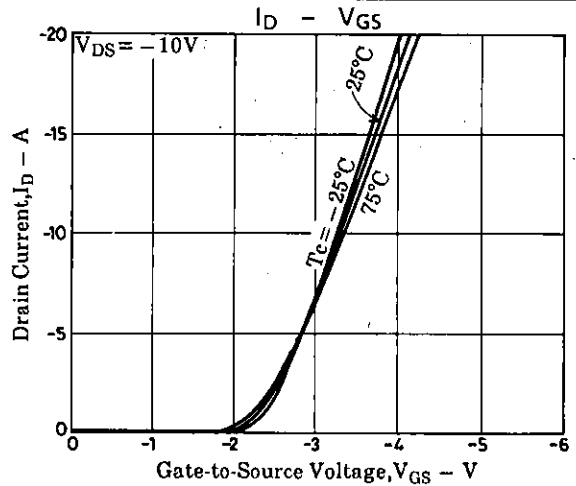
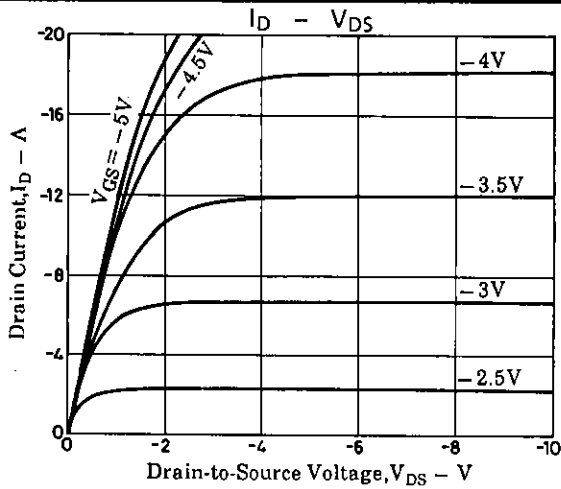
(unit : mm)



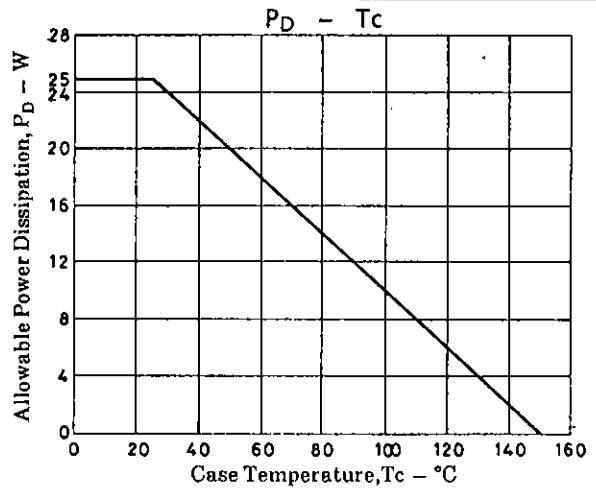
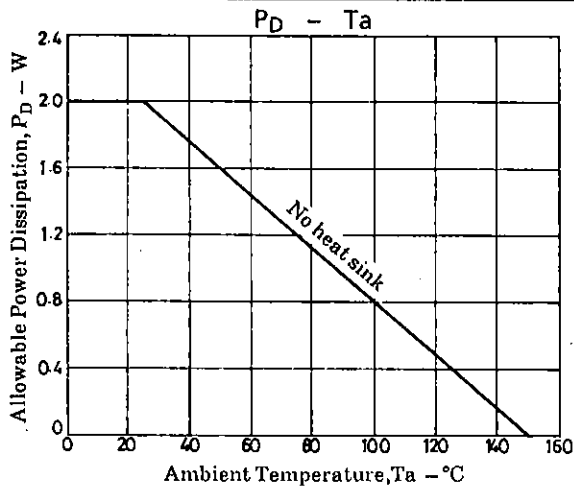
- 1 : Gate
- 2 : Drain
- 3 : Source

SANYO : TO-220ML





2SJ255



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